



AF/1fw

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Applicant:

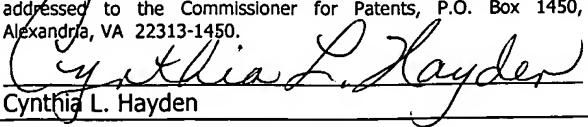
Chris E. Barns et al. § Art Unit: 2822
Serial No.: 10/629,127 § Examiner: Khanh B. Duong
Filed: July 29, 2003 § Docket: ITL.1016US
For: Preventing Silicide Formation at § Assignee: Intel Corporation
the Gate Electrode in a Replacement
Metal Gate Technology §

Mail Stop AF
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

REPLY TO FINAL REJECTION

Sir:

In response to the final rejection mailed August 8, 2005, please amend the above-referenced patent application as follows:

Date of Deposit: <u>August 26, 2005</u>
I hereby certify under 37 CFR 1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated above and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.
 Cynthia L. Hayden